

PRODUCT SUMMARY					
V _{DS} (V)	150				
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.052				
I _D (A)	25				
Configuration	Single				



N-Channel MOSFET

FEATURES

- TrenchFET® Power MOSFET
- Package with Low Thermal Resistance
- 100 % Rq and UIS Tested
- AEC-Q101 Qualified
- Material categorization:
 For definitions of compliance please see www.freescale.net.cn





ROHS COMPLIANT HALOGEN FREE

ORDERING INFOR	RMATION	
Package		TO-252
Lead (Pb)-free and Halog	en-free	SQD25N15-52-GE3

PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V_{DS}	150	V
Gate-Source Voltage		V _{GS}	± 20	V
Continuous Drain Current	T _C = 25 °C	- I _D	25	
	T _C = 125 °C		16	
Continuous Source Current (Diode Conduction) ^a		I _S	50	Α
Pulsed Drain Current ^b		I _{DM}	63	
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	30	
Single Pulse Avalanche Energy	L = 0.1 min	E _{AS}	45	mJ
Martin and Branco Biochastication b	T _C = 25 °C	D	107	W
Maximum Power Dissipation ^b	T _C = 125 °C	P_{D}	35	VV
Operating Junction and Storage Temperatur	e Range	T _J , T _{stg}	- 55 to + 175	°C

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-Ambient	PCB Mount ^c	R_{thJA}	50	°C/W	
Junction-to-Case (Drain)		R_{thJC}	1.4	C/VV	

Notes

- a. Package limited.
- b. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- c. When mounted on 1" square PCB (FR-4 material).



PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static						ı		
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$		150	-	=.	V	
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	$V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$		3	4	V	
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$		-	-	± 100	nA	
		V _{GS} = 0 V	V _{DS} = 150 V	-	-	1		
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V	V _{DS} = 150 V, T _J = 125 °C	-	-	50	μА	
		V _{GS} = 0 V	V _{DS} = 150 V, T _J = 175 °C	-	-	250		
On-State Drain Current ^a	I _{D(on)}	V _{GS} = 10 V	$V_{DS} \ge 5 V$	30	-	-	Α	
		V _{GS} = 10 V	I _D = 15 A	-	0.038	0.052	Ω	
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V	I _D = 15 A, T _J = 125 °C	-	-	0.104		
		V _{GS} = 10 V	I _D = 15 A, T _J = 175 °C	-	-	0.136		
Forward Transconductance ^b	9 _{fs}	V _{DS}	V _{DS} = 15 V, I _D = 15 A		33	-	S	
Dynamic ^b								
Input Capacitance	C _{iss}			-	1760	2200		
Output Capacitance	C _{oss}	$V_{GS} = 0 V$	$V_{GS} = 0 \text{ V}$ $V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$	-	215	270	pF	
Reverse Transfer Capacitance	C _{rss}			-	80	100		
Total Gate Charge ^c	Qg			-	34	51		
Gate-Source Charge ^c	Q_{gs}	V _{GS} = 10 V	$V_{DS} = 75 \text{ V}, I_D = 25 \text{ A}$	-	14.5	-	nC	
Gate-Drain Charge ^c	Q _{gd}]		-	5.4			
Gate Resistance	R _g	f = 1 MHz		1	1.8	2.6	Ω	
Turn-On Delay Time ^c	t _{d(on)}			=	11	17		
Rise Time ^c	t _r	$V_{DD} = 75 \text{ V}, \text{ R}_L = 3 \Omega$ $I_D \cong 25 \text{ A}, \text{ V}_{GEN} = 10 \text{ V}, \text{ R}_g = 1 \Omega$		-	11	17	ns	
Turn-Off Delay Time ^c	t _{d(off)}			=	20	30		
Fall Time ^c	t _f			=	6	9		
Source-Drain Diode Ratings and Chara	acteristics ^b							
Pulsed Current ^a	I _{SM}			I	-	63	Α	
Forward Voltage	V_{SD}	I _F = 20 A, V _{GS} = 0 V		-	0.87	1.5	V	

Notes

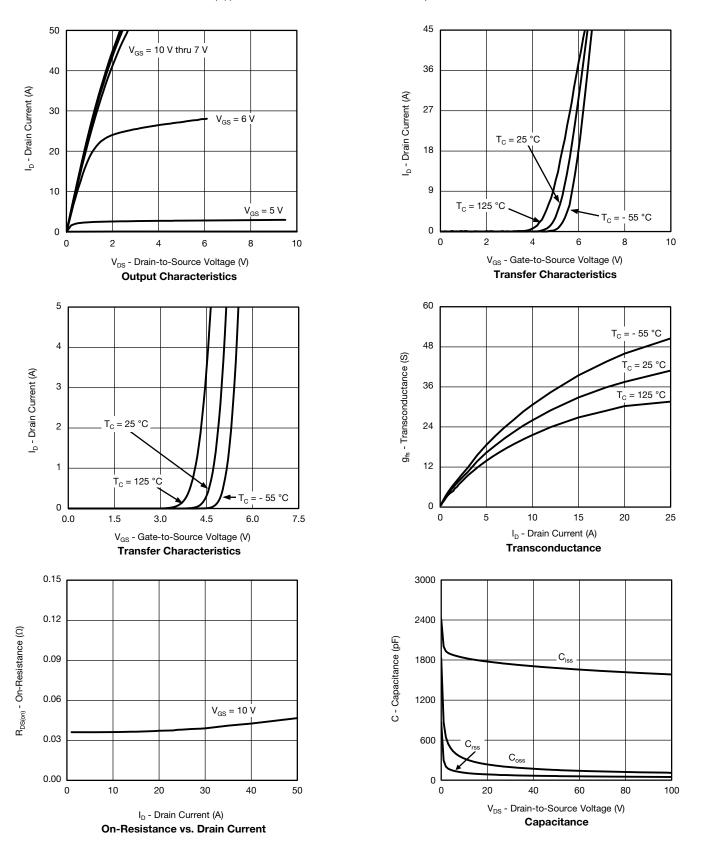
- a. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



Automotive N-Channel 150 V (D-S) 175 °C MOSFET

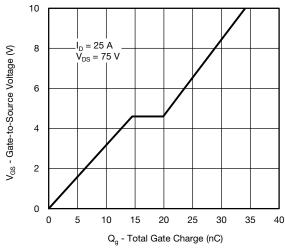
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



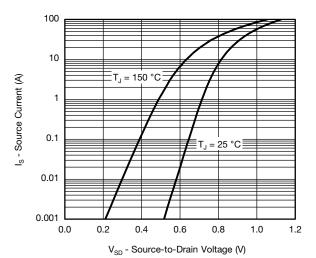


Automotive N-Channel 150 V (D-S) 175 °C MOSFET

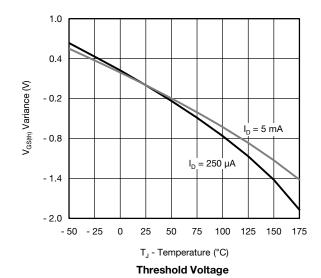
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



Gate Charge

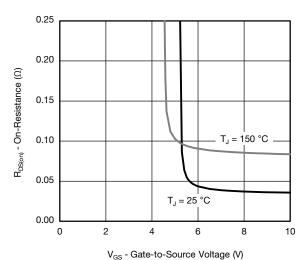


Source Drain Diode Forward Voltage

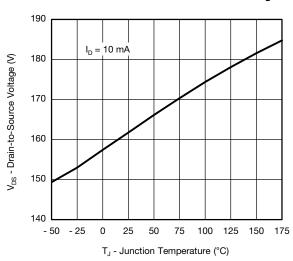


3.0 I_D = 5 A 2.5 R_{DS(on)} - On-Resistance (Normalized) 2.0 V_{GS} = 10 V 1.5 1.0 0.5 - 25 0 50 75 100 125 150 - 50 T_J - Junction Temperature (°C)

On-Resistance vs. Junction Temperature



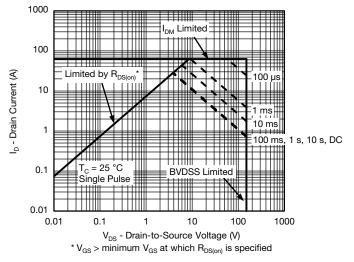
On-Resistance vs. Gate-to-Source Voltage



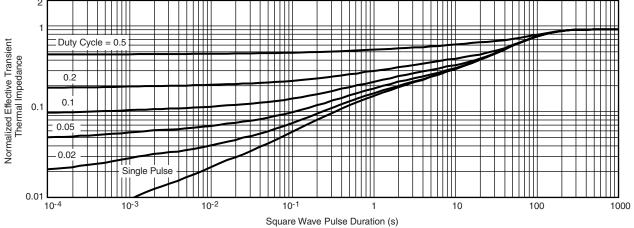
Drain Source Breakdown vs. Junction Temperature

Automotive N-Channel 150 V (D-S) 175 °C MOSFET

THERMAL RATINGS ($T_A = 25$ °C, unless otherwise noted)

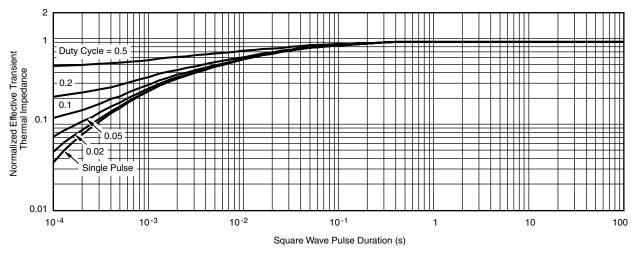


Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient

THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

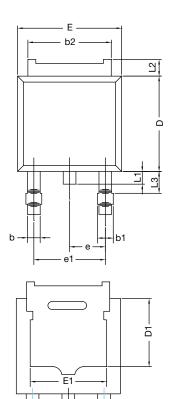
Note

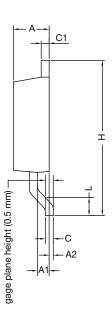
- The characteristics shown in the two graphs
- Normalized Transient Thermal Impedance Junction-to- Ambient (25 °C)
- Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Automotive N-Channel 150 V (D-S) 175 °C MOSFET

TO-252AA CASE OUTLINE



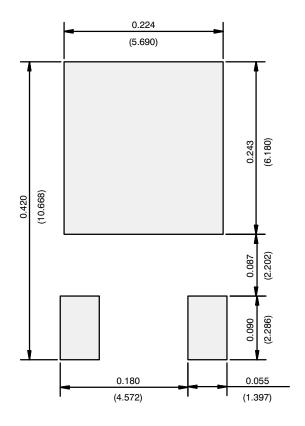


	MILLIMETERS		INC	HES		
DIM.	MIN.	MAX.	MIN.	MAX.		
Α	2.21	2.38	0.087	0.094		
A1	0.89	1.14	0.035	0.045		
A2	0.030	0.127	0.001	0.005		
b	0.71	0.88	0.028	0.035		
b1	0.76	1.14	0.030	0.045		
b2	5.23	5.44	0.206	0.214		
С	0.46	0.58	0.018	0.023		
C1	0.46	0.58	0.018	0.023		
D	5.97	6.22	0.235	0.245		
D1	4.10	4.45	0.161	0.175		
Е	6.48	6.73	0.255	0.265		
E1	4.49	5.50	0.177	0.217		
е	2.28	BSC	0.090 BSC			
e1	4.57	BSC	0.180 BSC			
Н	9.65	10.41	0.380	0.410		
L	1.40	1.78	0.055	0.070		
L1	0.64	1.02	0.025	0.040		
L2	0.89	1.27	0.035	0.050		
L3	1.15	1.52	0.040	0.060		
ECN: T11-0110-Rev. L, 18-Apr-11 DWG: 5347						

Note

• Dimension L3 is for reference only.

RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads Dimensions in Inches/(mm)

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Material Category Policy

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